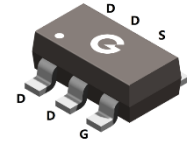
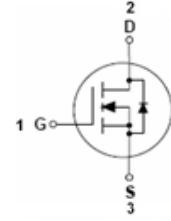


Features

- Electrostatic sensitive devices
- $R_{DS(ON)} < 26.5m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 32m\Omega$ @ $V_{GS} = 4.5V$
- $R_{DS(ON)} < 48m\Omega$ @ $V_{GS} = 2.5V$
- Halogen free
- Qualified to AEC-Q101 standards for high reliability

HF



SOT-23-6L

Mechanical Data

- Case: SOT-23-6L
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
TBL3400-6L	SOT-23-6L	3000 pcs / Tape & Reel	3400

Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	30	V
Gate-to-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current ($T_A = 25^\circ\text{C}$) *1	I_D	6.6	A
Continuous Drain Current ($T_A = 70^\circ\text{C}$) *1		5.2	A
Pulsed Drain Current ($t_p = 10\mu\text{s}$, $T_A = 25^\circ\text{C}$)	I_{DM}	30	A
Single Pulse Avalanche Energy *3	E_{AS}	7	mJ
Power Dissipation ($T_A = 25^\circ\text{C}$) *1	P_D	2	W
Operating Junction Temperature Range	T_J	$-55 \sim +150$	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	$-55 \sim +150$	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	30	40	$^\circ\text{C/W}$
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	-	62.5	$^\circ\text{C/W}$

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 30V, V _{GS} = 0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *2	V _{GS} = 10V, I _D = 5.7A	-	18	26.5	mΩ
		V _{GS} = 4.5V, I _D = 5A	-	22	32	
		V _{GS} = 2.5V, I _D = 3A	-	40	48	
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	0.7	0.8	1.4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	9	-	Ω
Dynamic Characteristics						
g _{FS}	Forward Transconductance	V _{DS} = 5V, I _D = 5.7A	-	26	-	S
C _{ISS}	Input Capacitance	V _{GS} = 0V	-	451	-	pF
C _{OSS}	Output Capacitance	V _{DS} = 15V	-	64	-	
C _{RSS}	Reverse Transfer Capacitance	f = 1.0MHz	-	59	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *4	V _{GS} = 10V V _{DD} = 15V R _L = 2.6Ω R _G = 3Ω	-	3.2	-	ns
t _r	Turn-on Rise Time *4		-	3.5	-	
t _{d(OFF)}	Turn-Off Delay Time *4		-	21.5	-	
t _f	Turn-Off Fall Time *4		-	2.7	-	
Q _G	Total Gate-Charge	V _{GS} = 4.5V	-	7	-	nC
Q _{GS}	Gate to Source Charge	V _{DS} = 15V	-	1.4	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 5.7A	-	2.2	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *2	I _S = 1A, V _{GS} = 0 V	-	0.7	1.0	V
t _{rr}	Body Diode Reverse Recovery Time	I _F = 5A, V _{GS} = 0 V	-	85	-	ns
Q _{rr}	Body Diode Reverse Recovery Charge	di/dt = 100A / μs	-	50	-	nC

Notes:

- The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper
- The data tested by pulsed, pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- The E_{AS} data shows Max. rating. The test condition is $V_{DD} = 15\text{V}, V_{GS} = 6\text{V}, L = 0.1\text{mH}$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

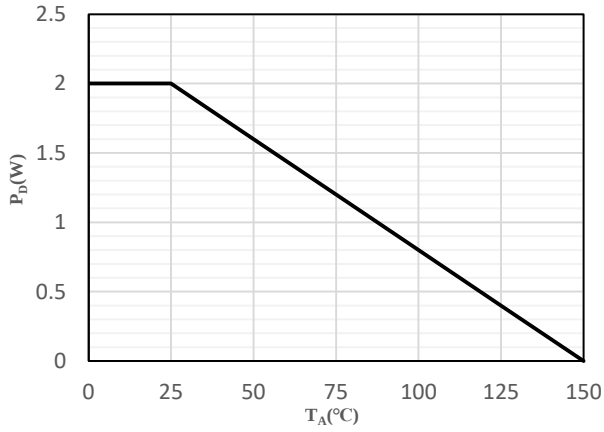


Fig 1 Power Dissipation

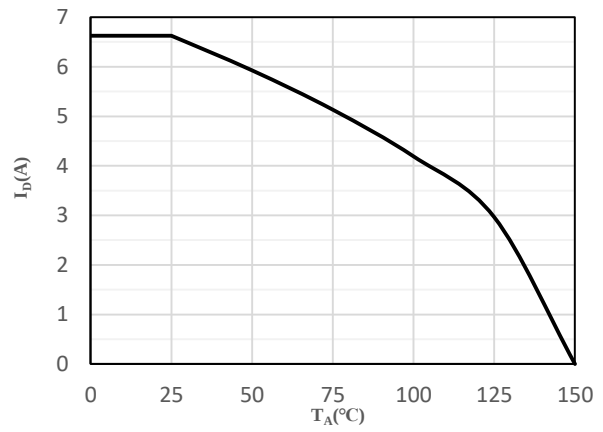


Fig 2 Drain Current

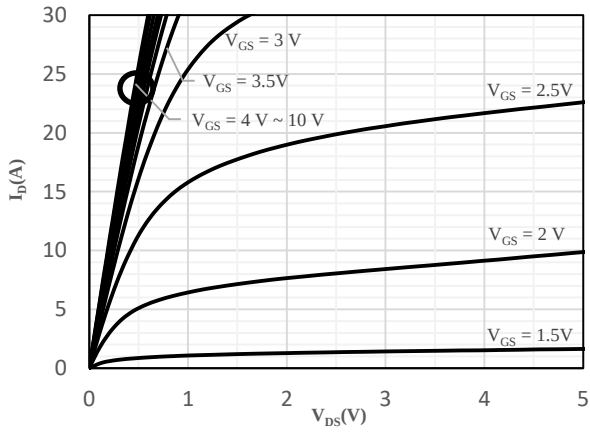


Fig 3 Typical Output Characteristics

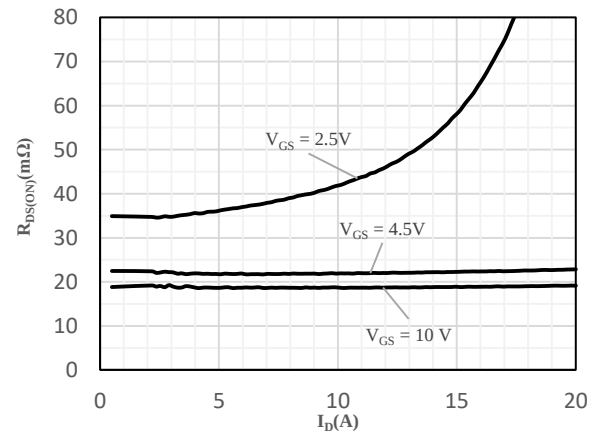


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

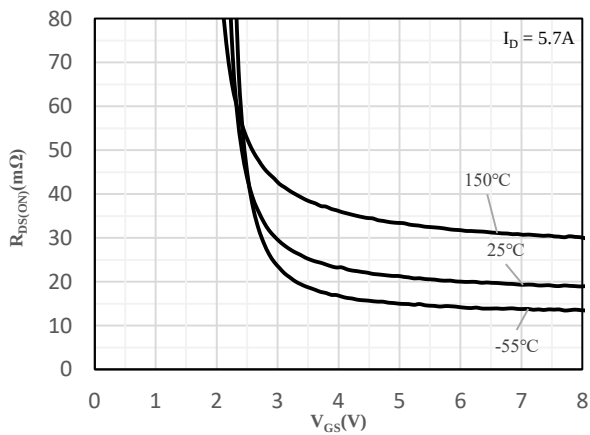


Fig 5 On-Resistance vs. Gate-Source Voltage

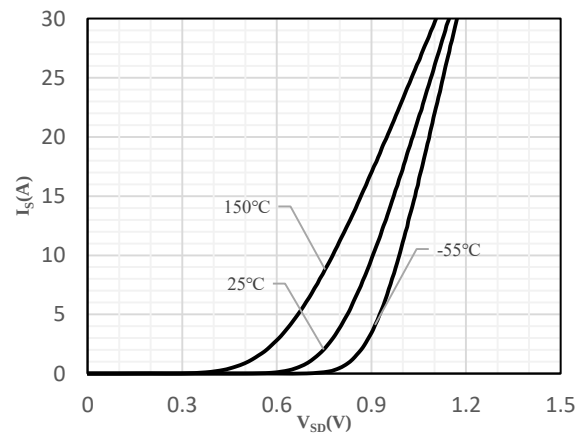


Fig 6 Body-Diode Characteristics

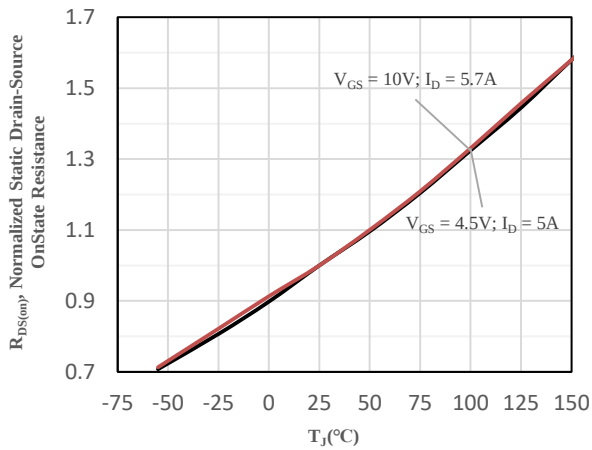


Fig 7 Normalized On-Resistance vs. Junction Temperature

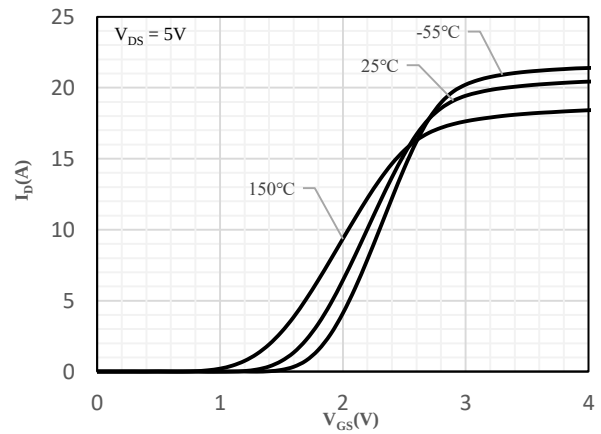


Fig 8 Transfer Characteristics

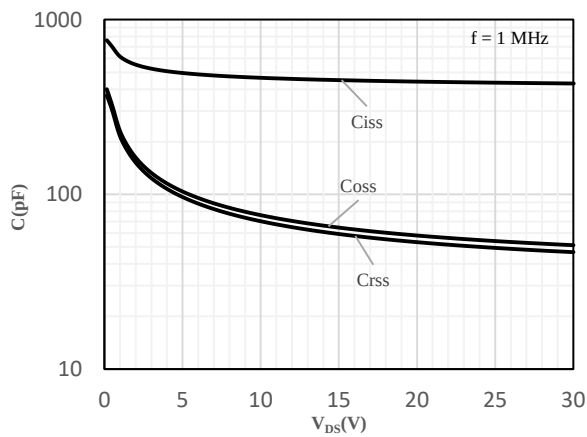


Fig 9 Capacitance Characteristics

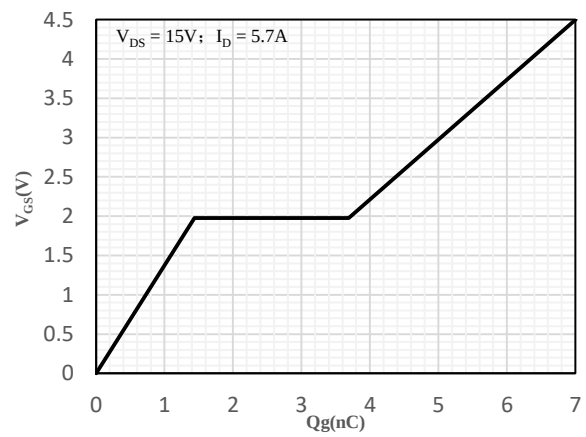


Fig 10 Gate-Charge Characteristics

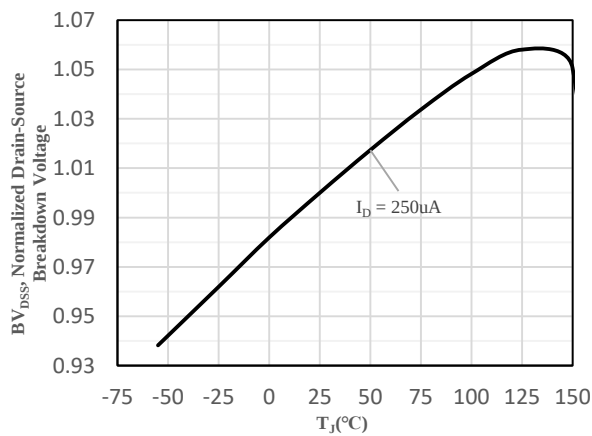


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

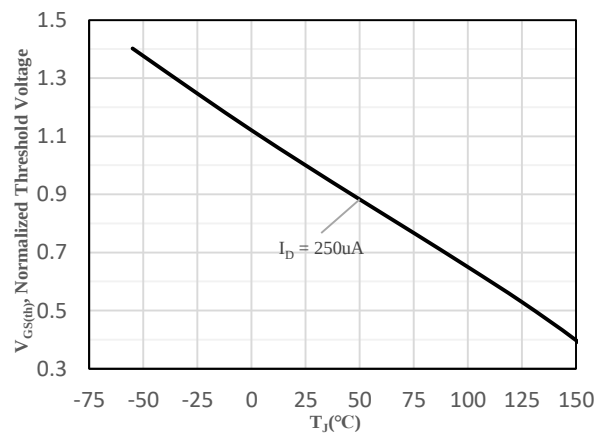
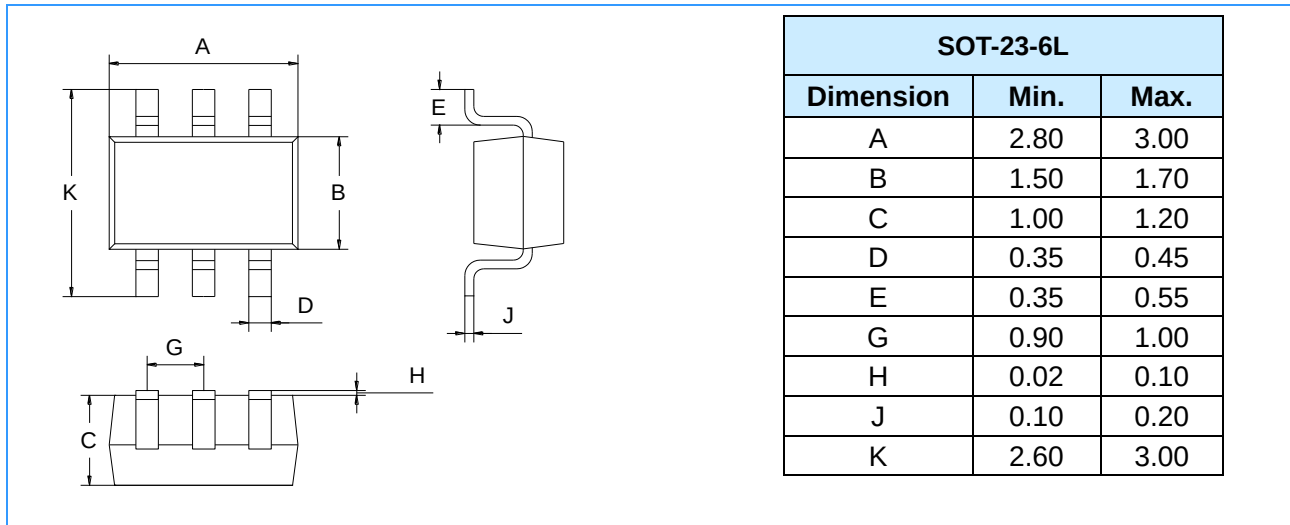
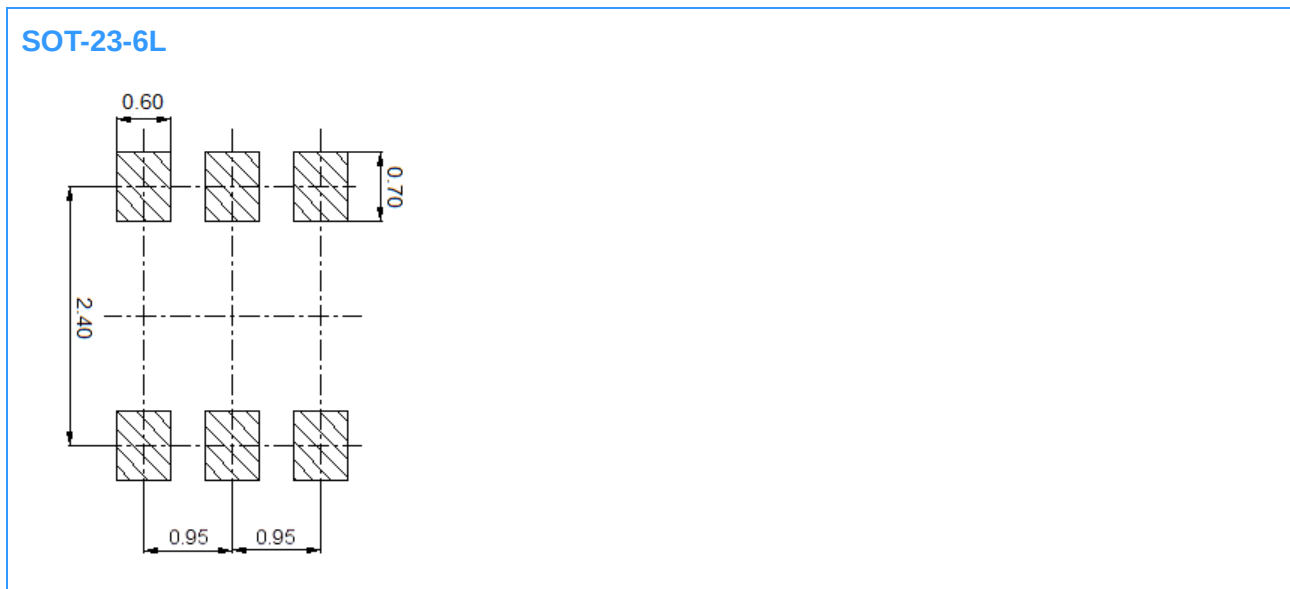


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

Package Outline Dimensions (Unit: mm)



Mounting Pad Layout (Unit: mm)



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